



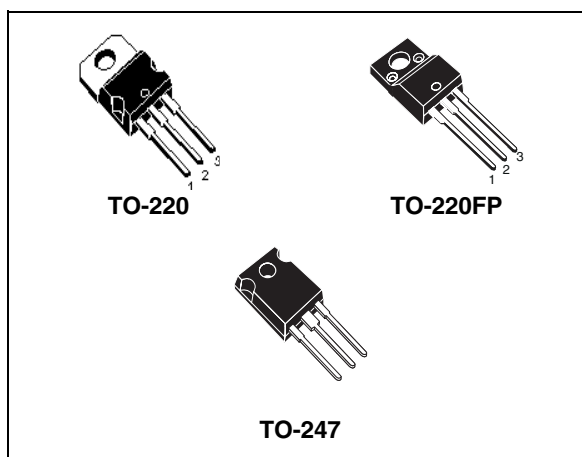
# STP8NK80Z - STP8NK80ZFP STW8NK80Z

N-channel 800V - 1.3Ω - 6.2A - TO-220 /TO-220FP/TO-247  
Zener-protected SuperMESH™ Power MOSFET

## General features

Type	V <sub>DSS</sub> (@T <sub>jmax</sub> )	R <sub>DS(on)</sub>	I <sub>D</sub>
STP8NK80Z	800 V	< 1.5 Ω	6.2 A
STP8NK80ZFP	800 V	< 1.5 Ω	6.2 A
STW8NK80Z	800 V	< 1.5 Ω	6.2 A

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability



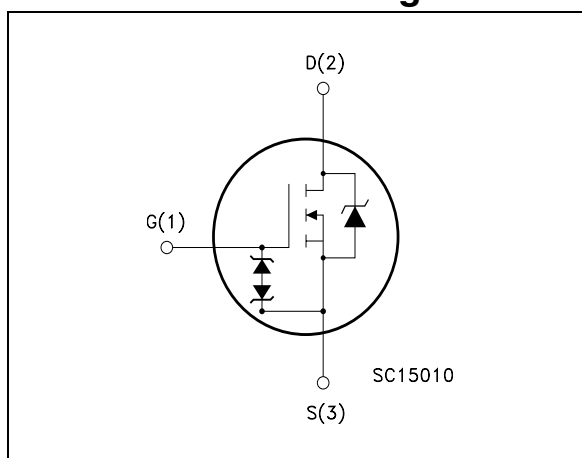
## Description

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

## Applications

- Switching application

## Internal schematic diagram



## Order codes

Part number	Marking	Package	Packaging
STP8NK80Z	P8NK80Z	TO-220	Tube
STP8NK80ZFP	P8NK80ZFP	TO-220FP	Tube
STW8NK80Z	W8NK80Z	TO-247	Tube

## Contents

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# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		STP8NK80Z STW8NK80Z	STP7NK80ZFP	
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	800		V
$V_{GS}$	Gate- source voltage	$\pm 30$		V
$I_D$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	6.2	6.2 <sup>(1)</sup>	A
$I_D$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	3.9	3.9 <sup>(1)</sup>	A
$I_{DM}^{(2)}$	Drain current (pulsed)	24.8	24.8 <sup>(1)</sup>	A
$P_{TOT}$	Total dissipation at $T_C = 25^\circ\text{C}$	140	30	W
	Derating factor	1.12	0.24	W/ $^\circ\text{C}$
$V_{ESD(G-S)}$	Gate source ESD(HBM-C=100pF, R=1.5K $\Omega$ )	4000		V
$dv/dt^{(3)}$	Peak diode recovery voltage slope	4.5		V/ns
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1s; $T_C = 25^\circ\text{C}$ )	-	2500	V
$T_j$ $T_{stg}$	Max operating Junction temperature Storage temperature	-55 to 150		$^\circ\text{C}$

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3.  $I_{SD} \leq 6.2$  A,  $di/dt \leq 200$  A/ $\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_j \leq T_{JMAX}$ .

**Table 2. Thermal data**

Symbol	Parameter	Value			Unit
		TO-220	TO-220FP	TO-247	
$R_{thj-case}$	Thermal resistance junction-case max	0.89	4.2	0.89	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5		50	$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose	300			$^\circ\text{C}$

**Table 3. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by Tj Max)	6.2	A
$E_{AS}$	Single pulse avalanche energy (starting Tj=25°C, Id=Iar, Vdd=50V)	300	mJ

**Table 4. Gate-source zener diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$BV_{GSO}$	Gate-source breakdown voltage	Igs=± 1mA (Open Drain)	30			V

## 1.1 Protection features of gate-to-source zener diodes

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}C$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	$I_D = 1MA, V_{GS} = 0$	800			V
$I_{DSS}$	Zero gate voltage Drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}, T_C = 125^{\circ}C$			1 50	$\mu A$ $\mu A$
$I_{GSS}$	Gate-body leakage Current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20 V$			$\pm 10$	$\mu A$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 100 \mu A$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 V, I_D = 3.1 A$		1.3	1.5	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15V, I_D = 3.1 A$		5.2		S
$C_{iss}$	Input capacitance	$V_{DS} = 25 V, f = 1 \text{ MHz},$ $V_{GS} = 0$		1320		pF
$C_{oss}$	Output capacitance			143		pF
$C_{rss}$	Reverse transfer capacitance			27		pF
$C_{oss \text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{DS} = 0V, V_{DS} = 0V \text{ to } 640V$		58		pF
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400 V, I_D = 3.1 A,$ $R_G = 4.7 \Omega, V_{GS} = 10 V$ (see <a href="#">Figure 20</a> )		17		ns
$t_r$	Rise time			30		ns
$t_{r(off)}$	Turn-off delay time			48		ns
$t_f$	Fall time			28		ns
$Q_g$	Total gate charge	$V_{DD} = 640 V, I_D = 65.2 A,$ $V_{GS} = 10 V$		46		nC
$Q_{gs}$	Gate-source charge			8.5		nC
$Q_{gd}$	Gate-drain charge			25		nC
$t_{r(Voff)}$	Off-voltage rise time	$V_{DD} = 640 V, I_D = 6.2 A,$ $R_G = 4.7 \Omega, V_{GS} = 10 V$ (see <a href="#">Figure 22</a> )		9		ns
$t_f$	Fall time			9		ns
$t_c$	Cross-over time			18		ns

1. Pulsed: pulse duration=300 $\mu s$ , duty cycle 1.5%

2.  $C_{oss \text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current				6.2	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				24.8	A
$V_{SD}^{(2)}$	Forward On voltage	$I_{SD} = 6.2 \text{ A}, V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 6.2 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 50 \text{ V}, T_j = 150^\circ\text{C}$ (see <a href="#">Figure 22</a> )		460		ns
$Q_{rr}$	Reverse recovery charge			2990		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current			13		A

1. Pulsed: pulse duration=300 $\mu\text{s}$ , duty cycle 1.5%
2. Pulse width limited by safe operating area

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220

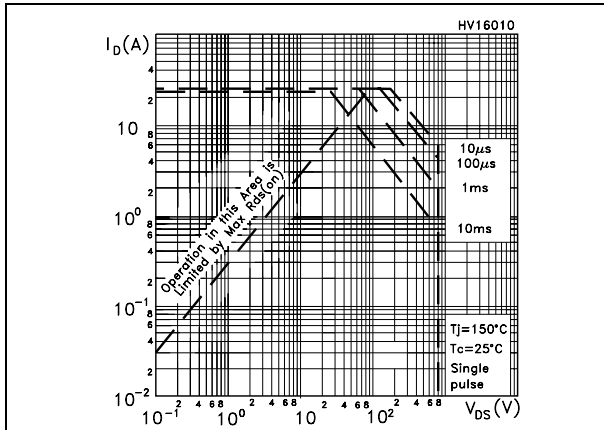


Figure 2. Thermal impedance for TO-220

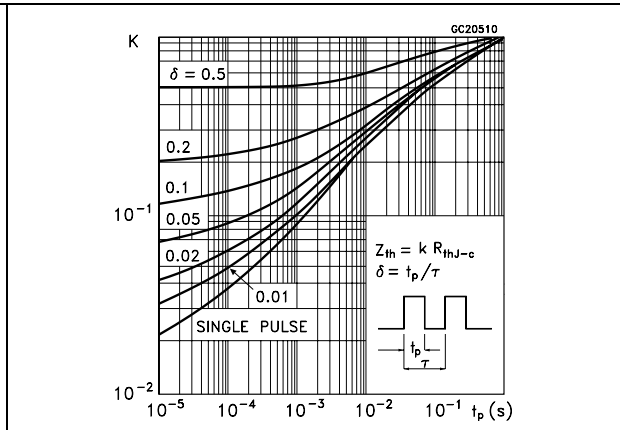


Figure 3. Safe operating area for TO-220FP

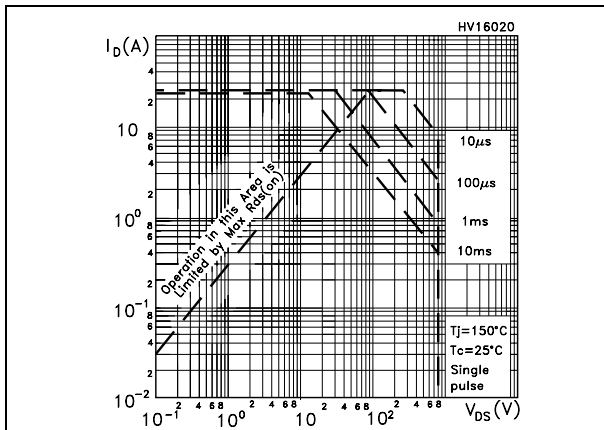


Figure 4. Thermal impedance for TO-220FP

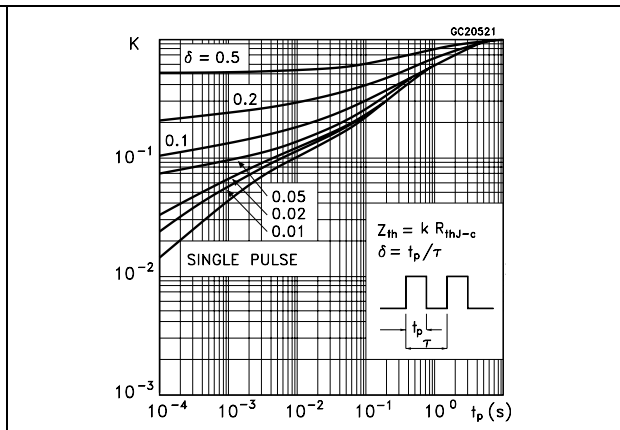


Figure 5. Safe operating area for TO-247 (HV16030)

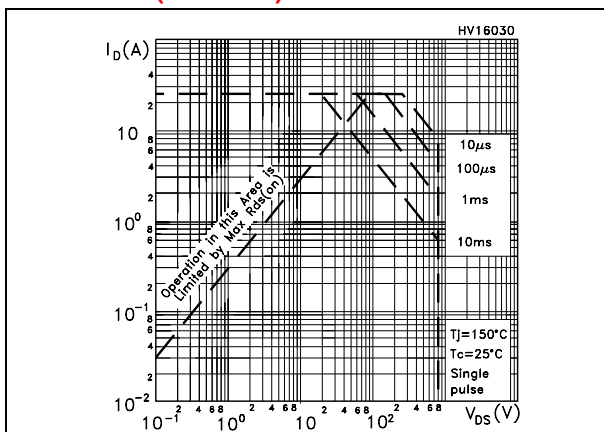


Figure 6. Thermal impedance for TO-247

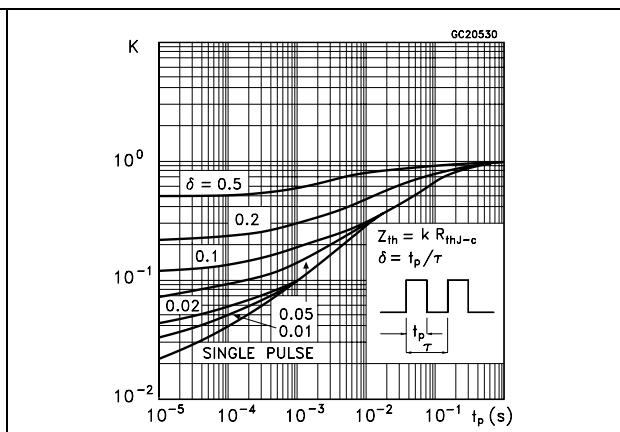


Figure 7. Output characteristics

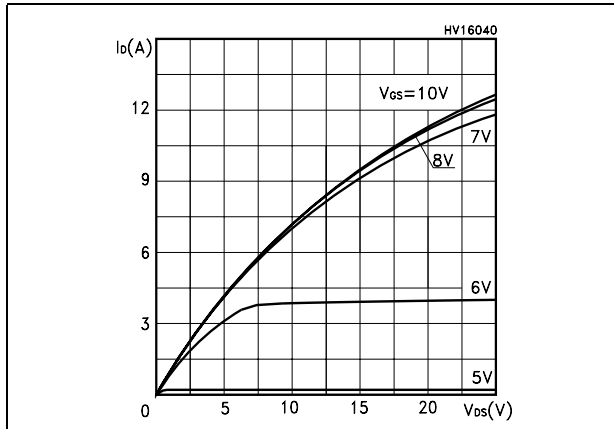


Figure 8. Transfer characteristics

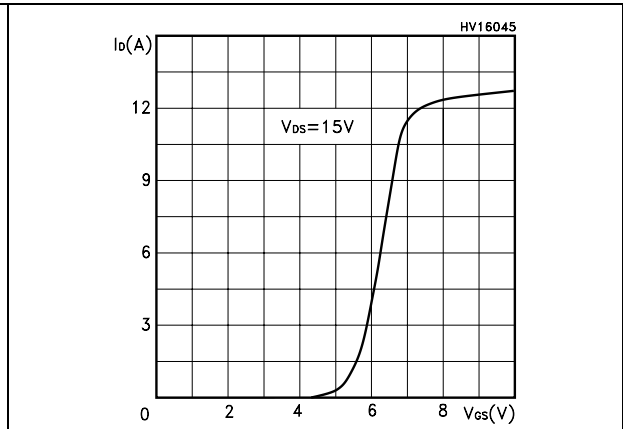


Figure 9. Transconductance

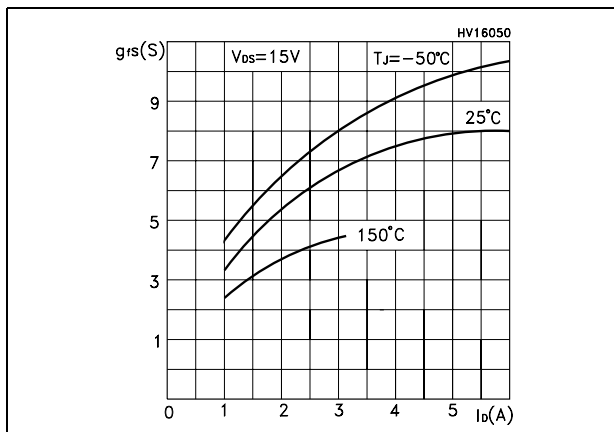


Figure 10. Static drain-source on resistance

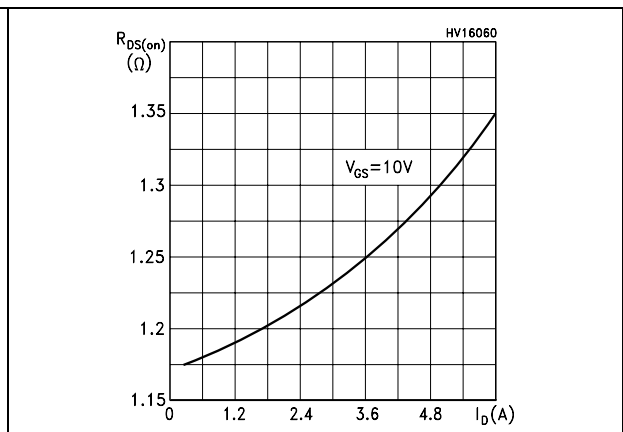


Figure 11. Gate charge vs gate-source voltage

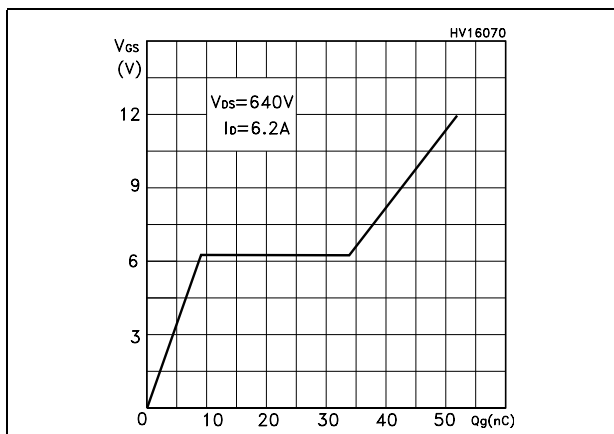


Figure 12. Capacitance variations

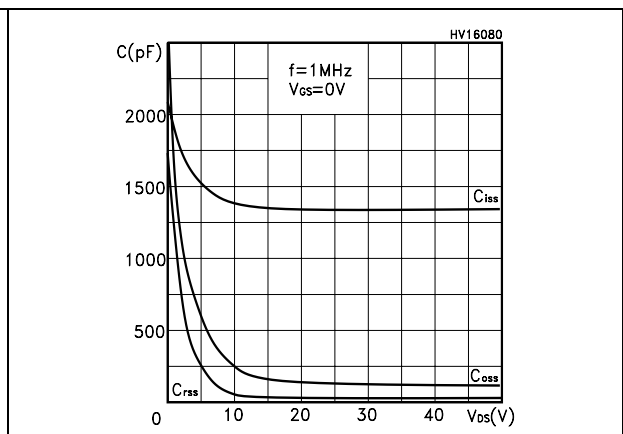




Figure 13. Normalized gate threshold voltage vs temperature

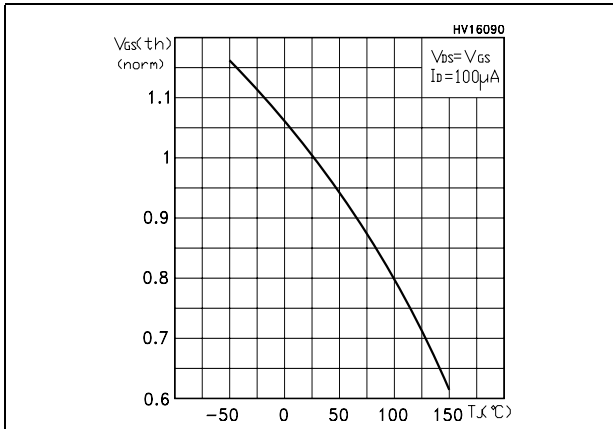


Figure 14. Normalized on resistance vs temperature

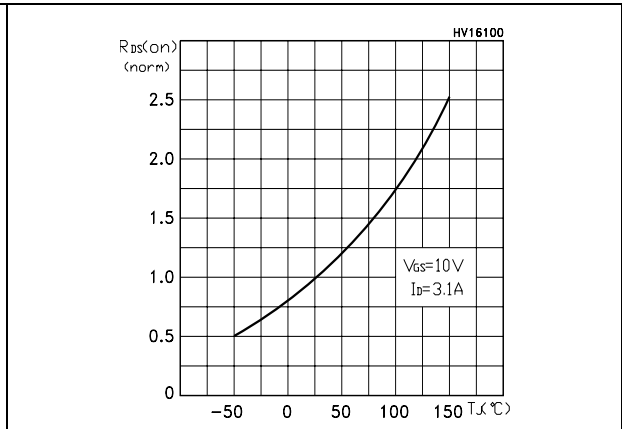


Figure 15. Source-drain diode forward characteristic

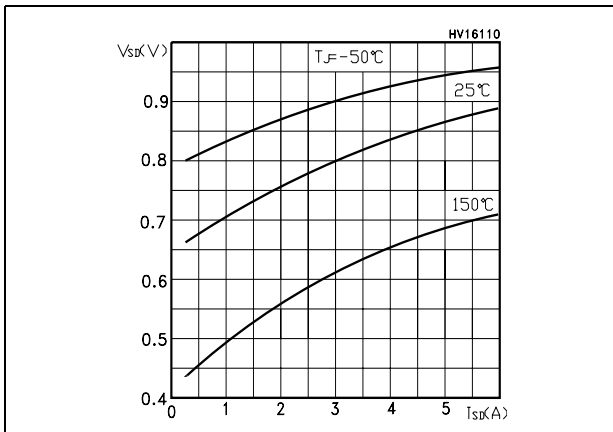


Figure 16. Normalized BV<sub>DSS</sub> vs temperature

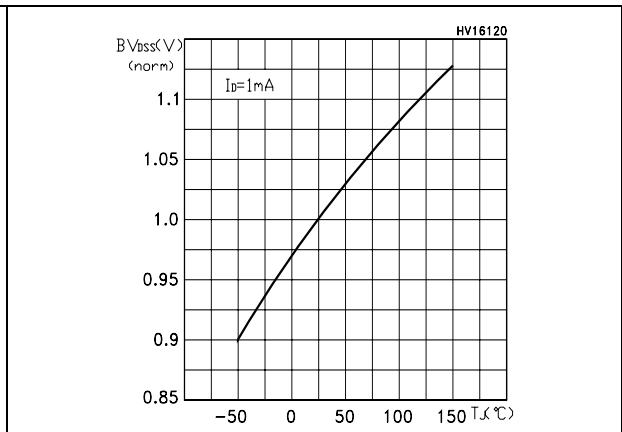
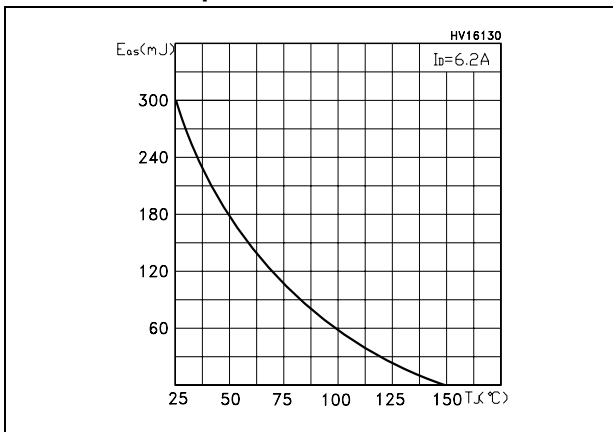


Figure 17. Maximum avalanche energy vs temperature



### 3 Test circuit

Figure 18. Unclamped inductive load test circuit

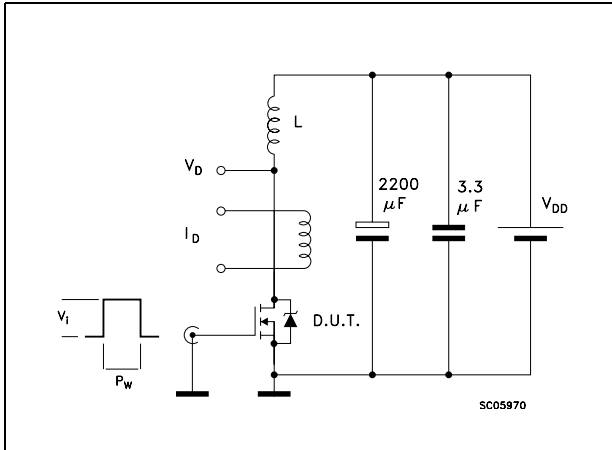


Figure 19. Unclamped inductive waveform

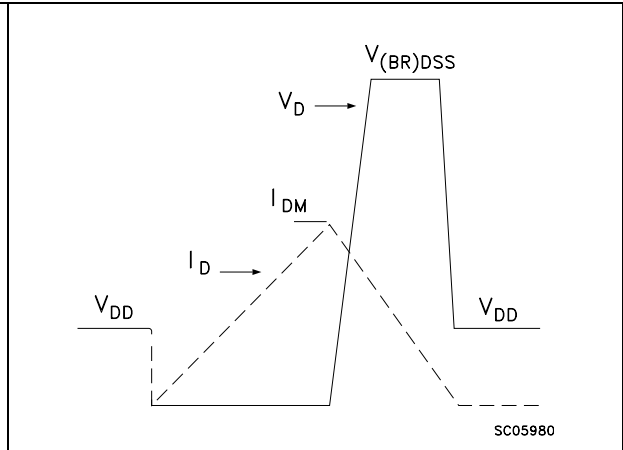


Figure 20. Switching times test circuit for resistive load

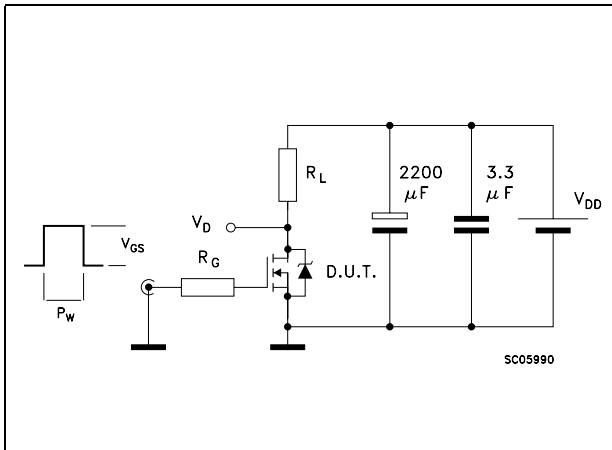


Figure 21. Gate charge test circuit

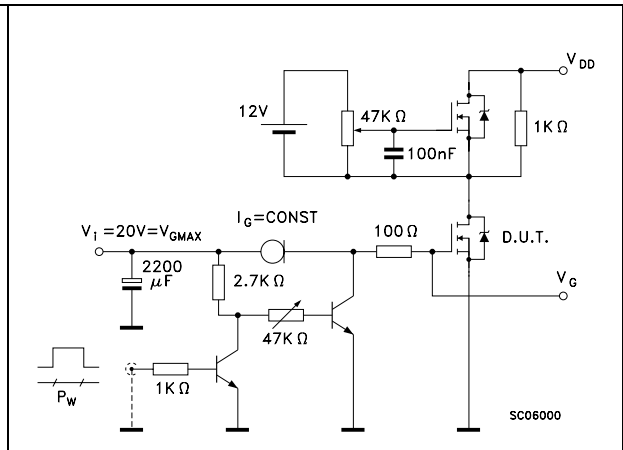
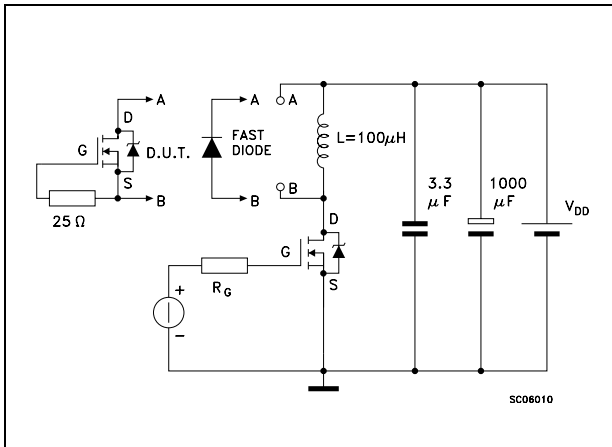


Figure 22. Test circuit for inductive load switching and diode recovery times

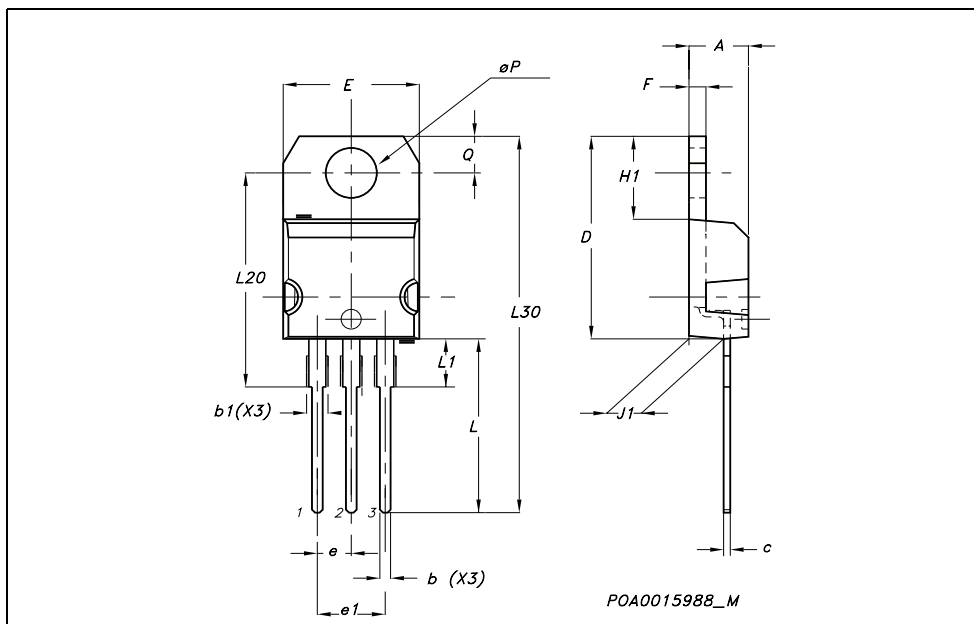


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

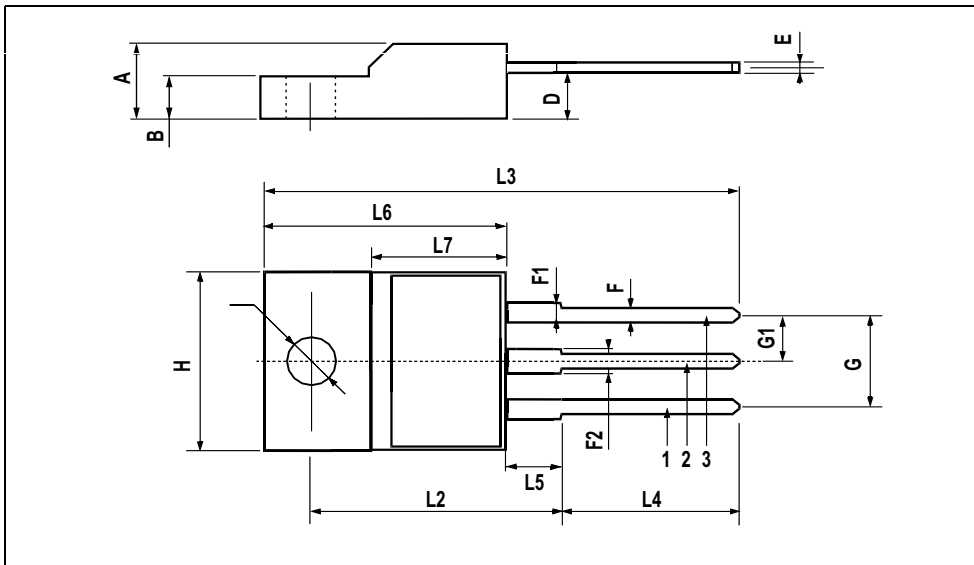
**TO-220 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



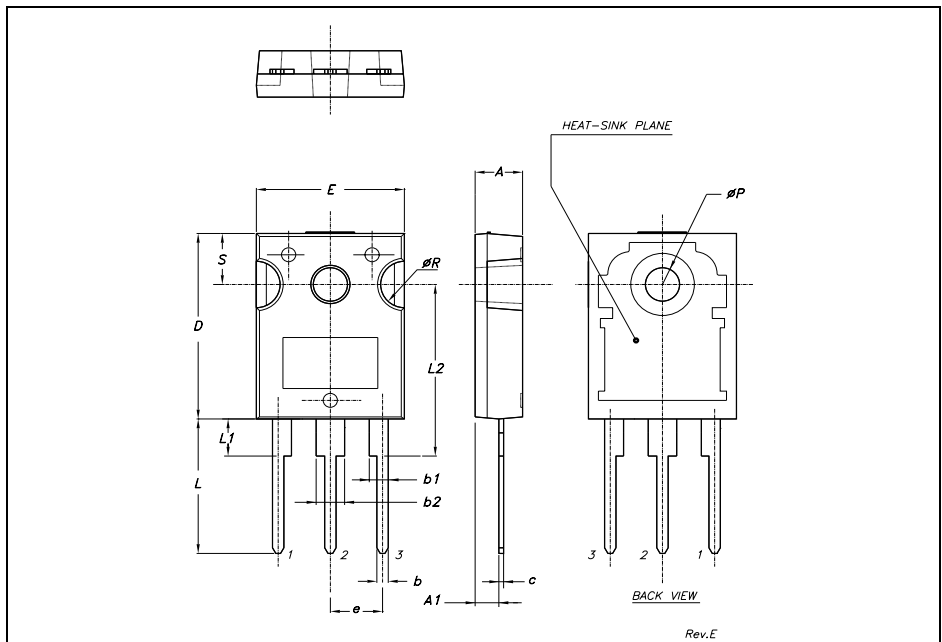
**TO-220FP MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



**TO-247 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



## 5 Revision history

**Table 8. Revision history**

Date	Revision	Changes
09-Sep-2004	2	Complete version
17-Aug-2006	3	New template, no content change

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